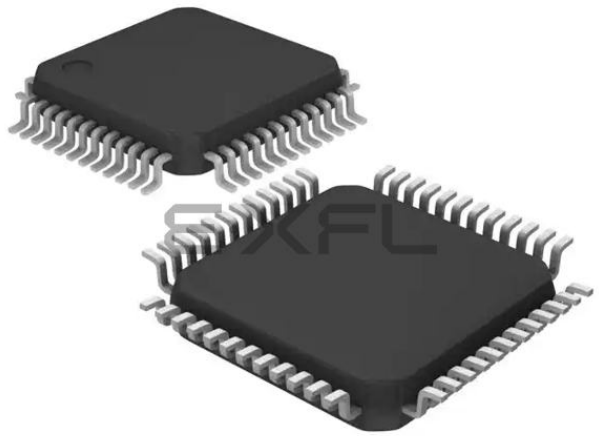
Renesas Electronics America Inc - R5F101GCAFB#V0 Datasheet



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What is "Embedded - Microcontrollers"?

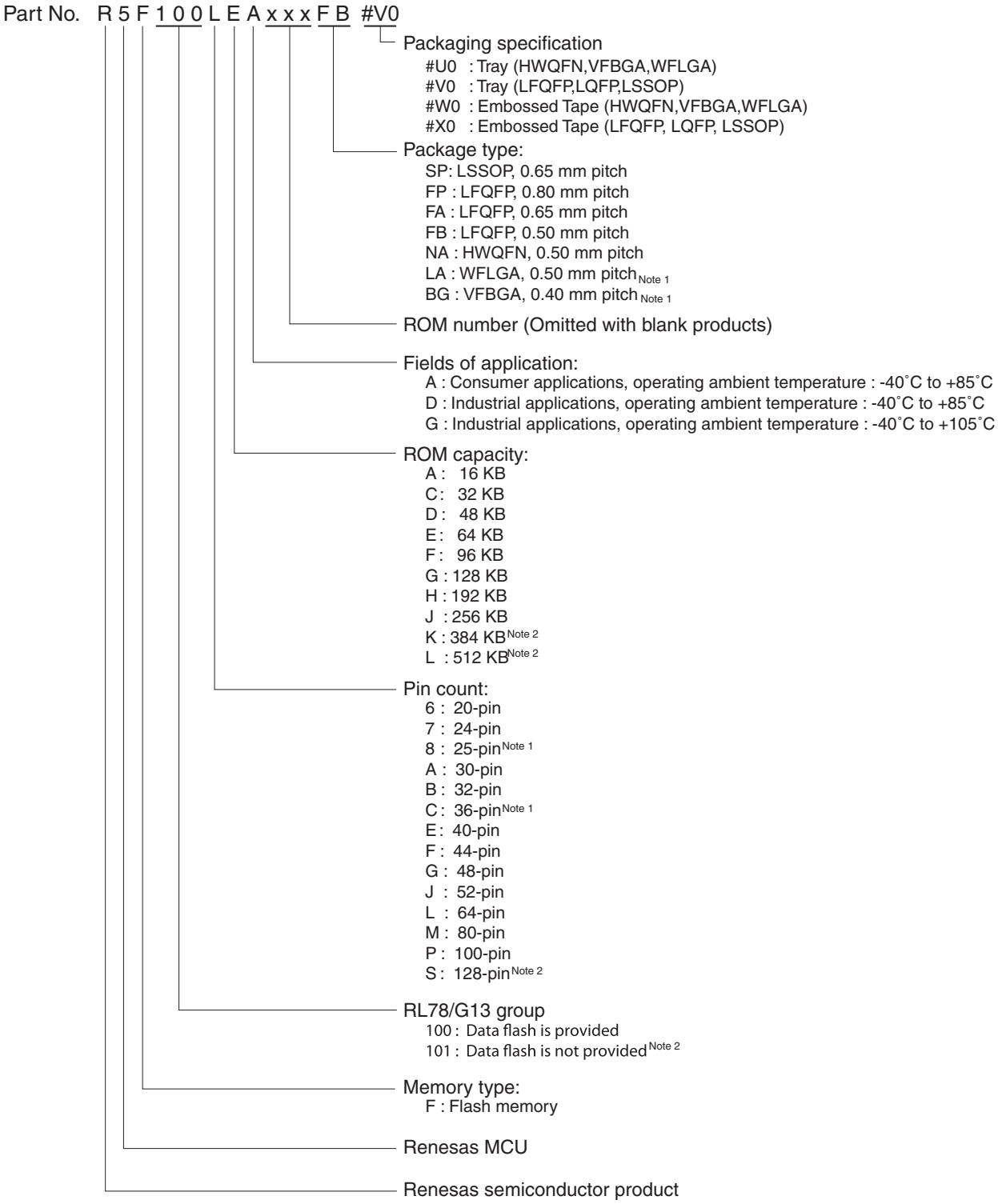
"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I²C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	34
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 10x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	48-LQFP
Supplier Device Package	48-LFQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f101gcafb-v0

1.2 List of Part Numbers

Figure 1-1. Part Number, Memory Size, and Package of RL78/G13

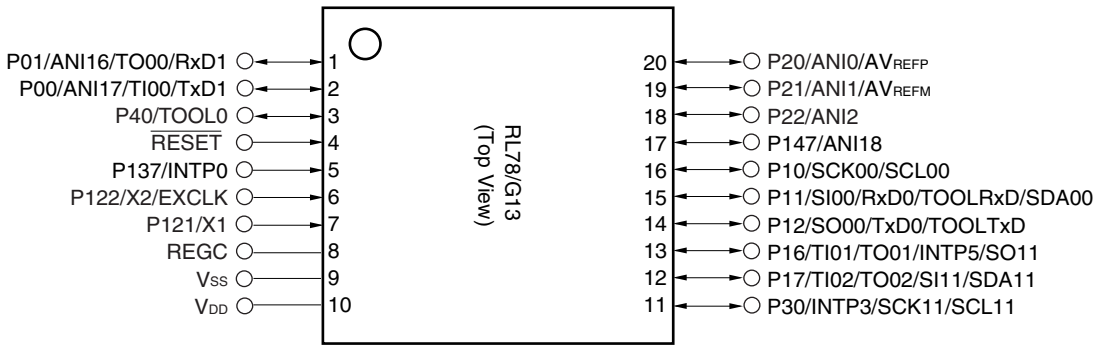


Notes
1. Products only for “A: Consumer applications (T_A = –40 to +85°C)”, and "G: Industrial applications (T_A = –40 to +105°C)"
2. Products only for “A: Consumer applications (T_A = –40 to +85°C)”, and "D: Industrial applications (T_A = –40 to +85°C)"

1.3 Pin Configuration (Top View)

1.3.1 20-pin products

- 20-pin plastic LSSOP (7.62 mm (300), 0.65 mm pitch)

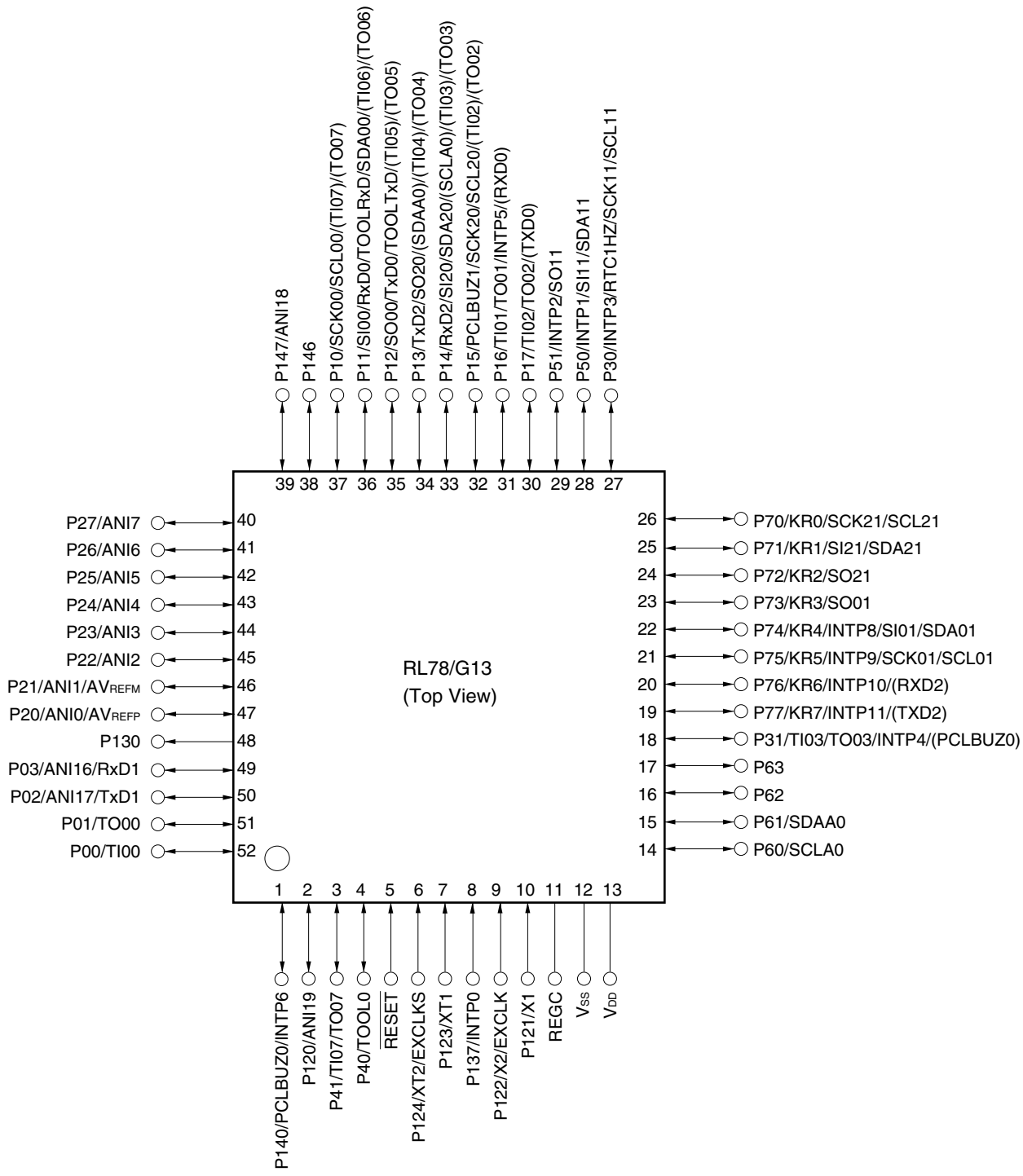


Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μF).

Remark For pin identification, see **1.4 Pin Identification**.

1.3.10 52-pin products

- 52-pin plastic LQFP (10 × 10 mm, 0.65 mm pitch)

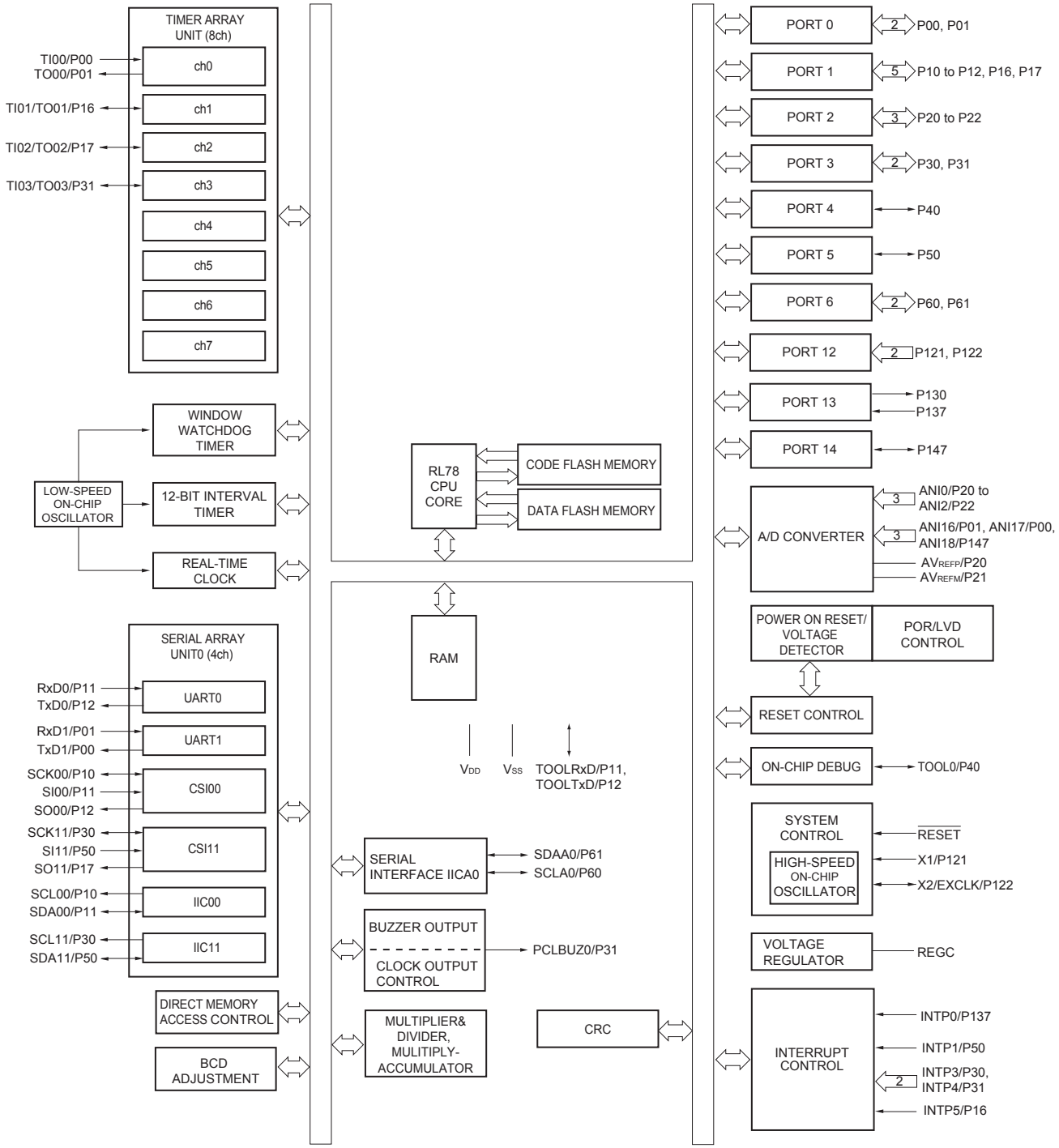


Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μF).

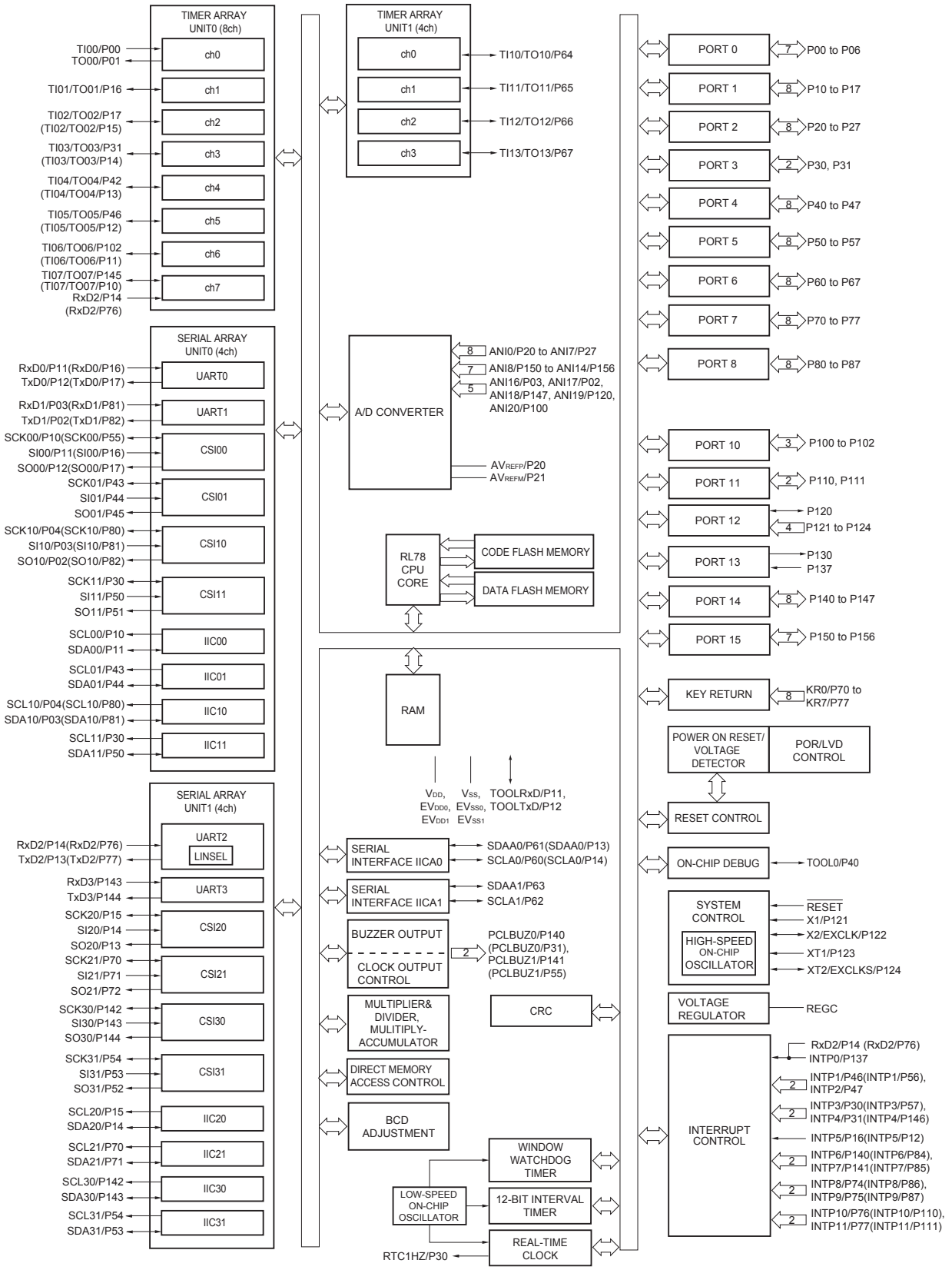
Remarks 1. For pin identification, see **1.4 Pin Identification**.

2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

1.5.3 25-pin products



1.5.13 100-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

1.6 Outline of Functions

[20-pin, 24-pin, 25-pin, 30-pin, 32-pin, 36-pin products]

Caution This outline describes the functions at the time when Peripheral I/O redirection register (PIOR) is set to 00H.

(1/2)

Item		20-pin		24-pin		25-pin		30-pin		32-pin		36-pin	
		R5F1006x	R5F1016x	R5F1007x	R5F1017x	R5F1008x	R5F1018x	R5F100Ax	R5F101Ax	R5F100Bx	R5F101Bx	R5F100Cx	R5F101Cx
Code flash memory (KB)		16 to 64		16 to 64		16 to 64		16 to 128		16 to 128		16 to 128	
Data flash memory (KB)		4	–	4	–	4	–	4 to 8	–	4 to 8	–	4 to 8	–
RAM (KB)		2 to 4 Note1		2 to 4 Note1		2 to 4 Note1		2 to 12 Note1		2 to 12 Note1		2 to 12 Note1	
Address space		1 MB											
Main system clock	High-speed system clock	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (High-speed main) mode: 1 to 20 MHz (V_{DD} = 2.7 to 5.5 V), HS (High-speed main) mode: 1 to 16 MHz (V_{DD} = 2.4 to 5.5 V), LS (Low-speed main) mode: 1 to 8 MHz (V_{DD} = 1.8 to 5.5 V), LV (Low-voltage main) mode: 1 to 4 MHz (V_{DD} = 1.6 to 5.5 V)											
	High-speed on-chip oscillator	HS (High-speed main) mode: 1 to 32 MHz (V_{DD} = 2.7 to 5.5 V), HS (High-speed main) mode: 1 to 16 MHz (V_{DD} = 2.4 to 5.5 V), LS (Low-speed main) mode: 1 to 8 MHz (V_{DD} = 1.8 to 5.5 V), LV (Low-voltage main) mode: 1 to 4 MHz (V_{DD} = 1.6 to 5.5 V)											
Subsystem clock		–											
Low-speed on-chip oscillator		15 kHz (TYP.)											
General-purpose registers		(8-bit register × 8) × 4 banks											
Minimum instruction execution time		0.03125 μs (High-speed on-chip oscillator: f_{IH} = 32 MHz operation)											
		0.05 μs (High-speed system clock: f_{MX} = 20 MHz operation)											
Instruction set		• Data transfer (8/16 bits) • Adder and subtractor/logical operation (8/16 bits) • Multiplication (8 bits × 8 bits) • Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc.											
I/O port	Total	16		20		21		26		28		32	
	CMOS I/O	13 (N-ch O.D. I/O [V_{DD} withstand voltage]: 5)		15 (N-ch O.D. I/O [V_{DD} withstand voltage]: 6)		15 (N-ch O.D. I/O [V_{DD} withstand voltage]: 6)		21 (N-ch O.D. I/O [V_{DD} withstand voltage]: 9)		22 (N-ch O.D. I/O [V_{DD} withstand voltage]: 9)		26 (N-ch O.D. I/O [V_{DD} withstand voltage]: 10)	
	CMOS input	3		3		3		3		3		3	
	CMOS output	–		–		1		–		–		–	
	N-ch O.D. I/O (withstand voltage: 6 V)	–		2		2		2		3		3	
Timer	16-bit timer	8 channels											
	Watchdog timer	1 channel											
	Real-time clock (RTC)	1 channel Note 2											
	12-bit interval timer (IT)	1 channel											
	Timer output	3 channels (PWM outputs: 2 Note 3)		4 channels (PWM outputs: 3 Note 3)				4 channels (PWM outputs: 3 Note 3), 8 channels (PWM outputs: 7 Note 3) Note 4					
	RTC output	–											

Notes 1. The flash library uses RAM in self-programming and rewriting of the data flash memory.
The target products and start address of the RAM areas used by the flash library are shown below.
R5F100xD, R5F101xD (x = 6 to 8, A to C): Start address FF300H
R5F100xE, R5F101xE (x = 6 to 8, A to C): Start address FEF00H
For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

2. Only the constant-period interrupt function when the low-speed on-chip oscillator clock (f_{IL}) is selected

2.2 Oscillator Characteristics

2.2.1 X1, XT1 oscillator characteristics

(T_A = −40 to +85°C, 1.6 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation frequency (f_X)Note	Ceramic resonator/ crystal resonator	2.7 V ≤ V_{DD} ≤ 5.5 V	1.0		20.0	MHz
		2.4 V ≤ V_{DD} < 2.7 V	1.0		16.0	MHz
		1.8 V ≤ V_{DD} < 2.4 V	1.0		8.0	MHz
		1.6 V ≤ V_{DD} < 1.8 V	1.0		4.0	MHz
XT1 clock oscillation frequency (f_X)Note	Crystal resonator		32	32.768	35	kHz

Note Indicates only permissible oscillator frequency ranges. Refer to AC Characteristics for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

Remark When using the X1 oscillator and XT1 oscillator, refer to **5.4 System Clock Oscillator**.

2.2.2 On-chip oscillator characteristics

(T_A = −40 to +85°C, 1.6 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Oscillators	Parameters	Conditions		MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequencyNotes 1, 2	f_{IH}			1		32	MHz
High-speed on-chip oscillator clock frequency accuracy		−20 to +85 °C	1.8 V ≤ V_{DD} ≤ 5.5 V	−1.0		+1.0	%
			1.6 V ≤ V_{DD} < 1.8 V	−5.0		+5.0	%
		−40 to −20 °C	1.8 V ≤ V_{DD} ≤ 5.5 V	−1.5		+1.5	%
			1.6 V ≤ V_{DD} < 1.8 V	−5.5		+5.5	%
Low-speed on-chip oscillator clock frequency	f_{IL}				15		kHz
Low-speed on-chip oscillator clock frequency accuracy				−15		+15	%

Notes 1. High-speed on-chip oscillator frequency is selected by bits 0 to 3 of option byte (000C2H/010C2H) and bits 0 to 2 of HOCODIV register.

2. This indicates the oscillator characteristics only. Refer to AC Characteristics for instruction execution time.

2.3 DC Characteristics

2.3.1 Pin characteristics

(T_A = −40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) (1/5)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high Note 1	I_{OH1}	Per pin for P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	1.6 V ≤ EV_{DD0} ≤ 5.5 V			−10.0 Note 2	mA
		Total of P00 to P04, P07, P32 to P37, P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145 (When duty ≤ 70% Note 3)	4.0 V ≤ EV_{DD0} ≤ 5.5 V			−55.0	mA
			2.7 V ≤ EV_{DD0} < 4.0 V			−10.0	mA
			1.8 V ≤ EV_{DD0} < 2.7 V			−5.0	mA
			1.6 V ≤ EV_{DD0} < 1.8 V			−2.5	mA
		Total of P05, P06, P10 to P17, P30, P31, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147 (When duty ≤ 70% Note 3)	4.0 V ≤ EV_{DD0} ≤ 5.5 V			−80.0	mA
			2.7 V ≤ EV_{DD0} < 4.0 V			−19.0	mA
			1.8 V ≤ EV_{DD0} < 2.7 V			−10.0	mA
			1.6 V ≤ EV_{DD0} < 1.8 V			−5.0	mA
		Total of all pins (When duty ≤ 70% Note 3)	1.6 V ≤ EV_{DD0} ≤ 5.5 V			−135.0 Note 4	mA
	I_{OH2}	Per pin for P20 to P27, P150 to P156	1.6 V ≤ V_{DD} ≤ 5.5 V			−0.1 Note 2	mA
		Total of all pins (When duty ≤ 70% Note 3)	1.6 V ≤ V_{DD} ≤ 5.5 V			−1.5	mA

Notes 1. Value of current at which the device operation is guaranteed even if the current flows from the EV_{DD0}, EV_{DD1}, V_{DD} pins to an output pin.

2. However, do not exceed the total current value.

3. Specification under conditions where the duty factor ≤ 70%.
The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = (I_{OH} × 0.7)/(n × 0.01)

<Example> Where n = 80% and I_{OH} = −10.0 mA

Total output current of pins = (−10.0 × 0.7)/(80 × 0.01) ≅ −8.7 mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

4. The applied current for the products for industrial application (R5F100xxDxx, R5F101xxDxx, R5F100xxGxx) is −100 mA.

Caution P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

Notes 1. Total current flowing into V_{DD} and EV_{DD0}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD}, EV_{DD0} or V_{SS}, EV_{SS0}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

2. When high-speed on-chip oscillator and subsystem clock are stopped.

3. When high-speed system clock and subsystem clock are stopped.

4. When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.

5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: 2.7 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 32 MHz
2.4 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 16 MHz
LS (low-speed main) mode: 1.8 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 8 MHz
LV (low-voltage main) mode: 1.6 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 4 MHz

Remarks 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

2. f_{IH}: High-speed on-chip oscillator clock frequency

3. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)

4. Except subsystem clock operation, temperature condition of the TYP. value is T_A = 25°C

Notes 1. Total current flowing into V_{DD} and EV_{DD0}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD}, EV_{DD0} or V_{SS}, EV_{SS0}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

2. During HALT instruction execution by flash memory.

3. When high-speed on-chip oscillator and subsystem clock are stopped.

4. When high-speed system clock and subsystem clock are stopped.

5. When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.

6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.

7. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: 2.7 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 32 MHz
2.4 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 16 MHz
LS (low-speed main) mode: 1.8 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 8 MHz
LV (low-voltage main) mode: 1.6 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 4 MHz

8. Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.

Remarks 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

2. f_{IH}: High-speed on-chip oscillator clock frequency

3. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)

4. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is T_A = 25°C

Notes 1. Total current flowing into V_{DD}, EV_{DD0}, and EV_{DD1}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD}, EV_{DD0}, and EV_{DD1}, or V_{SS}, EV_{SS0}, and EV_{SS1}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

2. When high-speed on-chip oscillator and subsystem clock are stopped.

3. When high-speed system clock and subsystem clock are stopped.

4. When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the 12-bit interval timer and watchdog timer.

5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: 2.7 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 32 MHz
2.4 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 16 MHz
LS (low-speed main) mode: 1.8 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 8 MHz
LV (low-voltage main) mode: 1.6 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 4 MHz

Remarks 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

2. f_{IH}: High-speed on-chip oscillator clock frequency

3. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)

4. Except subsystem clock operation, temperature condition of the TYP. value is T_A = 25°C

Note The following conditions are required for low voltage interface when $EV_{DD0} < V_{DD}$

1.8 V ≤ EV_{DD0} < 2.7 V : MIN. 125 ns

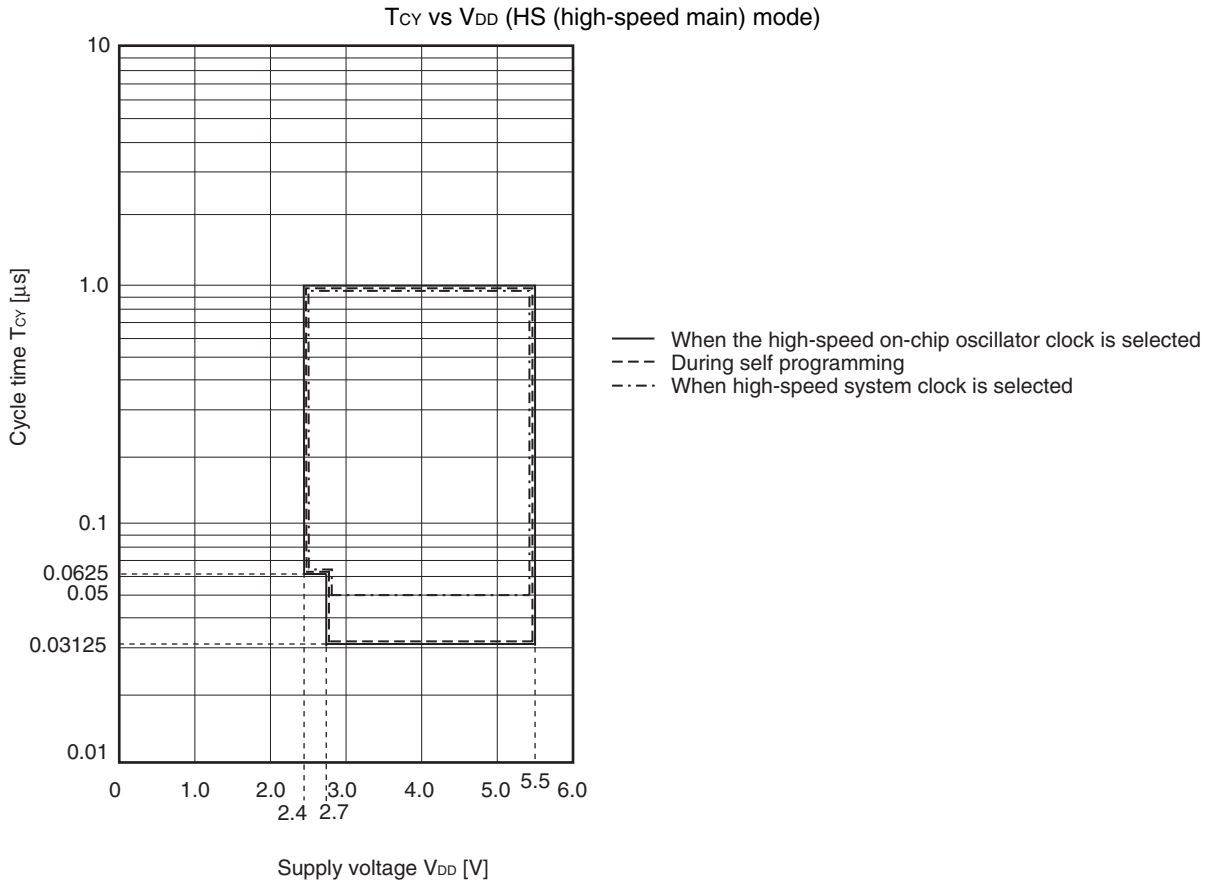
1.6 V ≤ EV_{DD0} < 1.8 V : MIN. 250 ns

Remark f_{MCK}: Timer array unit operation clock frequency

(Operation clock to be set by the CKSmn0, CKSmn1 bits of timer mode register mn (TMRmn).

m: Unit number (m = 0, 1), n: Channel number (n = 0 to 7))

Minimum Instruction Execution Time during Main System Clock Operation



(4) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input) (2/2)

(T_A = –40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SIp setup time (to SCKp↑) Note 1	t_{SIK2}	2.7 V ≤ EV_{DD0} ≤ 5.5 V		1/f_{MCK}+20		1/f_{MCK}+30		1/f_{MCK}+30		ns
		1.8 V ≤ EV_{DD0} ≤ 5.5 V		1/f_{MCK}+30		1/f_{MCK}+30		1/f_{MCK}+30		ns
		1.7 V ≤ EV_{DD0} ≤ 5.5 V		1/f_{MCK}+40		1/f_{MCK}+40		1/f_{MCK}+40		ns
		1.6 V ≤ EV_{DD0} ≤ 5.5 V		—		1/f_{MCK}+40		1/f_{MCK}+40		ns
SIp hold time (from SCKp↑) Note 2	t_{KSI2}	1.8 V ≤ EV_{DD0} ≤ 5.5 V		1/f_{MCK}+31		1/f_{MCK}+31		1/f_{MCK}+31		ns
		1.7 V ≤ EV_{DD0} ≤ 5.5 V		1/f_{MCK}+250		1/f_{MCK}+250		1/f_{MCK}+250		ns
		1.6 V ≤ EV_{DD0} ≤ 5.5 V		—		1/f_{MCK}+250		1/f_{MCK}+250		ns
Delay time from SCKp↓ to SOp output Note 3	t_{KSO2}	C = 30 pF Note 4	2.7 V ≤ EV_{DD0} ≤ 5.5 V		2/f_{MCK}+44		2/f_{MCK}+110		2/f_{MCK}+110	ns
			2.4 V ≤ EV_{DD0} ≤ 5.5 V		2/f_{MCK}+75		2/f_{MCK}+110		2/f_{MCK}+110	ns
			1.8 V ≤ EV_{DD0} ≤ 5.5 V		2/f_{MCK}+110		2/f_{MCK}+110		2/f_{MCK}+110	ns
			1.7 V ≤ EV_{DD0} ≤ 5.5 V		2/f_{MCK}+220		2/f_{MCK}+220		2/f_{MCK}+220	ns
			1.6 V ≤ EV_{DD0} ≤ 5.5 V		—		2/f_{MCK}+220		2/f_{MCK}+220	ns

Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

4. C is the load capacitance of the SOp output lines.

5. Transfer rate in the SNOOZE mode: MAX. 1 Mbps

Caution Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM number (g = 0, 1, 4, 5, 8, 14)

2. f_{MCK}: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

Notes 1. Excludes quantization error (±1/2 LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. When $AV_{REFP} < V_{DD}$, the MAX. values are as follows.
Overall error: Add ±1.0 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.
Zero-scale error/Full-scale error: Add ±0.05%FSR to the MAX. value when $AV_{REFP} = V_{DD}$.
Integral linearity error/ Differential linearity error: Add ±0.5 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.

4. Values when the conversion time is set to 57 μs (min.) and 95 μs (max.).

5. Refer to **2.6.2 Temperature sensor/internal reference voltage characteristics**.

2.6.5 Power supply voltage rising slope characteristics

(T_A = –40 to +85°C, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	S_{VDD}				54	V/ms

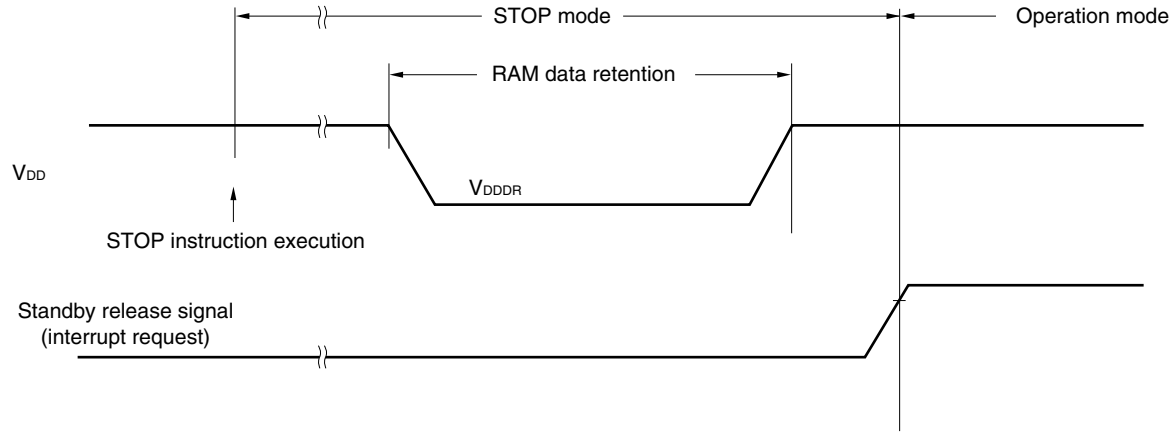
Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until V_{DD} reaches the operating voltage range shown in 2.4 AC Characteristics.

2.7 RAM Data Retention Characteristics

(T_A = –40 to +85°C, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	V_{DDDR}		1.46[Note]		5.5	V

Note This depends on the POR detection voltage. For a falling voltage, data in RAM are retained until the voltage reaches the level that triggers a POR reset but not once it reaches the level at which a POR reset is generated.



Notes 1. Transfer rate in the SNOOZE mode : MAX. 1 Mbps

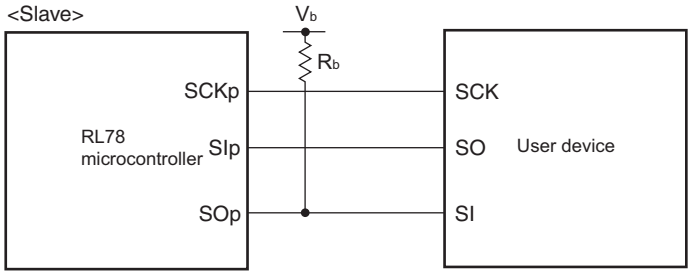
2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

4. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the SIp pin and SCKp pin and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/EV_{DD} tolerance (for the 64- to 128-pin products)) mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

CSI mode connection diagram (during communication at different potential)



Remarks 1. R_b[Ω]:Communication line (SOp) pull-up resistance, C_b[F]: Communication line (SOp) load capacitance, V_b[V]: Communication line voltage

2. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 00, 01, 02,
10, 12, 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)

3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).
m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13))

4. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

(3) When reference voltage (+) = V_{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (–) = V_{SS} (ADREFM = 0), target pin : ANI0 to ANI14, ANI16 to ANI26, internal reference voltage, and temperature sensor output voltage

(T_A = –40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V, Reference voltage (+) = V_{DD}, Reference voltage (–) = V_{SS})

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error[Note 1]	AINL	10-bit resolution	2.4 V ≤ V_{DD} ≤ 5.5 V		1.2	±7.0	LSB
Conversion time	t_{CONV}	10-bit resolution Target pin: ANI0 to ANI14, ANI16 to ANI26	3.6 V ≤ V_{DD} ≤ 5.5 V	2.125		39	μs
			2.7 V ≤ V_{DD} ≤ 5.5 V	3.1875		39	μs
			2.4 V ≤ V_{DD} ≤ 5.5 V	17		39	μs
		10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	3.6 V ≤ V_{DD} ≤ 5.5 V	2.375		39	μs
			2.7 V ≤ V_{DD} ≤ 5.5 V	3.5625		39	μs
			2.4 V ≤ V_{DD} ≤ 5.5 V	17		39	μs
Zero-scale error[Notes 1, 2]	E_{ZS}	10-bit resolution	2.4 V ≤ V_{DD} ≤ 5.5 V			±0.60	%FSR
Full-scale error[Notes 1, 2]	E_{FS}	10-bit resolution	2.4 V ≤ V_{DD} ≤ 5.5 V			±0.60	%FSR
Integral linearity error[Note 1]	ILE	10-bit resolution	2.4 V ≤ V_{DD} ≤ 5.5 V			±4.0	LSB
Differential linearity error[Note 1]	DLE	10-bit resolution	2.4 V ≤ V_{DD} ≤ 5.5 V			±2.0	LSB
Analog input voltage	V_{AIN}	ANI0 to ANI14		0		V_{DD}	V
		ANI16 to ANI26		0		EV_{DD0}	V
		Internal reference voltage output (2.4 V ≤ V_{DD} ≤ 5.5 V, HS (high-speed main) mode)		V_{BGR}[Note 3]			V
		Temperature sensor output voltage (2.4 V ≤ V_{DD} ≤ 5.5 V, HS (high-speed main) mode)		V_{TMPS25}[Note 3]			V

Notes 1. Excludes quantization error (±1/2 LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

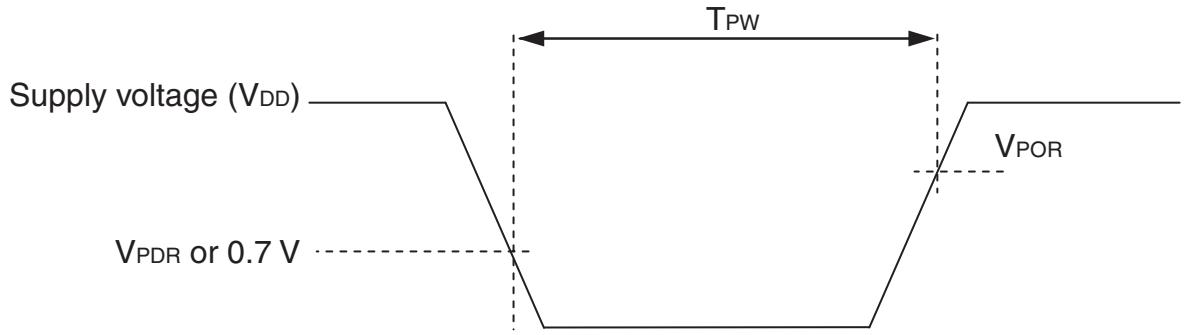
3. Refer to **3.6.2 Temperature sensor/internal reference voltage characteristics**.

3.6.3 POR circuit characteristics

(T_A = –40 to +105°C, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	V_{POR}	Power supply rise time	1.45	1.51	1.57	V
	V_{PDR}	Power supply fall time	1.44	1.50	1.56	V
Minimum pulse width	T_{PW}		300			μs

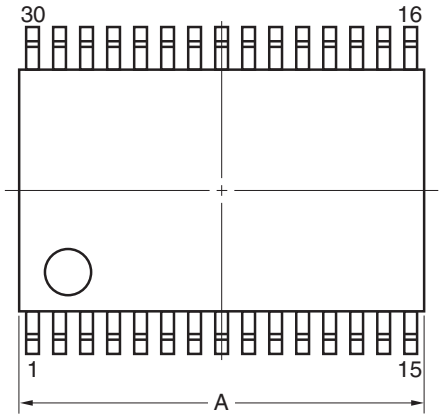
Note Minimum time required for a POR reset when V_{DD} exceeds below V_{PDR}. This is also the minimum time required for a POR reset from when V_{DD} exceeds below 0.7 V to when V_{DD} exceeds V_{POR} while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).



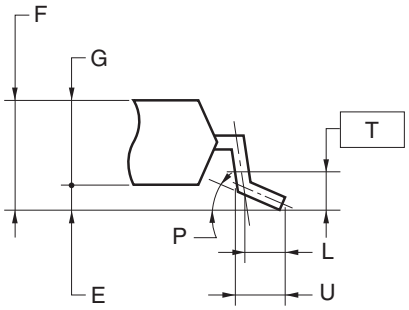
4.4 30-pin Products

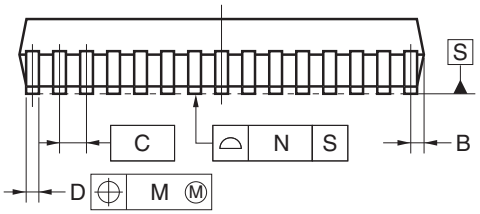
R5F100AAASP, R5F100ACASP, R5F100ADASP, R5F100AEASP, R5F100AFASP, R5F100AGASP
R5F101AAASP, R5F101ACASP, R5F101ADASP, R5F101AEASP, R5F101AFASP, R5F101AGASP
R5F100AADSP, R5F100ACDSP, R5F100ADDSP, R5F100AEDSP, R5F100AFDSP, R5F100AGDSP
R5F101AADSP, R5F101ACDSP, R5F101ADDSP, R5F101AEDSP, R5F101AFDSP, R5F101AGDSP
R5F100AAGSP, R5F100ACGSP, R5F100ADGSP,R5F100AEGSP, R5F100AFGSP, R5F100AGGSP

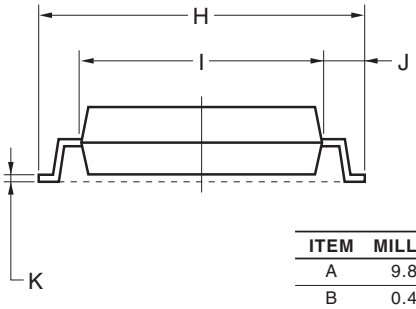
JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LSSOP30-0300-0.65	PLSP0030JB-B	S30MC-65-5A4-3	0.18



detail of lead end







NOTE
Each lead centerline is located within 0.13 mm of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS
A	9.85±0.15
B	0.45 MAX.
C	0.65 (T.P.)
D	$0.24^{+0.08}_{-0.07}$
E	0.1±0.05
F	1.3±0.1
G	1.2
H	8.1±0.2
I	6.1±0.2
J	1.0±0.2
K	0.17±0.03
L	0.5
M	0.13
N	0.10
P	$3^{\circ}{}^{+5^{\circ}}_{-3^{\circ}}$
T	0.25
U	0.6±0.15

Rev.	Date	Description	
		Page	Summary
3.00	Aug 02, 2013	81	Modification of figure of AC Timing Test Points
		81	Modification of description and note 3 in (1) During communication at same potential (UART mode)
		83	Modification of description in (2) During communication at same potential (CSI mode)
		84	Modification of description in (3) During communication at same potential (CSI mode)
		85	Modification of description in (4) During communication at same potential (CSI mode) (1/2)
		86	Modification of description in (4) During communication at same potential (CSI mode) (2/2)
		88	Modification of table in (5) During communication at same potential (simplified I^2C mode) (1/2)
		89	Modification of table and caution in (5) During communication at same potential (simplified I^2C mode) (2/2)
		91	Modification of table and notes 1 and 4 in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2)
		92, 93	Modification of table and notes 2 to 7 in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)
		94	Modification of remarks 1 to 4 in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)
		95	Modification of table in (7) Communication at different potential (2.5 V, 3 V) (CSI mode) (1/2)
		96	Modification of table and caution in (7) Communication at different potential (2.5 V, 3 V) (CSI mode) (2/2)
		97	Modification of table in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (1/3)
		98	Modification of table, note 1, and caution in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (2/3)
		99	Modification of table, note 1, and caution in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (3/3)
		100	Modification of remarks 3 and 4 in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (3/3)
		102	Modification of table in (9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (1/2)
		103	Modification of table and caution in (9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (2/2)
		106	Modification of table in (10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I^2C mode) (1/2)
		107	Modification of table, note 1, and caution in (10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I^2C mode) (2/2)
		109	Addition of (1) I^2C standard mode
		111	Addition of (2) I^2C fast mode
		112	Addition of (3) I^2C fast mode plus
		112	Modification of IICA serial transfer timing
		113	Addition of table in 2.6.1 A/D converter characteristics
		113	Modification of description in 2.6.1 (1)
		114	Modification of notes 3 to 5 in 2.6.1 (1)
		115	Modification of description and notes 2, 4, and 5 in 2.6.1 (2)
		116	Modification of description and notes 3 and 4 in 2.6.1 (3)
		117	Modification of description and notes 3 and 4 in 2.6.1 (4)